

TRANSMITTAL

Electronic Version v1.1

Stylesheet Version v1.1.0

Title of Invention	Method for Manufacturing Buried Insulating Layer Type Single Crystal Silicon Carbide Substrate and Manufacturing Device for the Same	
Application Number :		
Date :		
First Named Applicant:	Katsutoshi IZUMI	
Confirmation Number:		
Attorney Docket Number:	040091	
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Submitted By:		Elec. Sign.
Mr. Mel R. Quintos Registered Number: 31898		/MRQ/ Attorney

Documents being submitted:	Files
us-assignment	U040091-usassn.xml us-assignment.xsl us-assignment.dtd asn1.tif
us-request	U040091-usrequ.xml us-request.dtd us-request.xsl
us-fee-sheet	U040091-usfees.xml us-fee-sheet.xsl us-fee-sheet.dtd
us-declaration application-body	dec3.tif spec2-trans.xml us-application-body.xsl application-body.dtd wipo.ent mathml2.dtd mathml2-qname-1.mod isoamsa.ent isoamsb.ent isoamsc.ent isoamsn.ent isoamso.ent isoamsr.ent isogr3.ent isomfrk.ent isomopf.ent isomscr.ent isotech.ent isobox.ent isocyr1.ent isocyr2.ent isodia.ent isolat1.ent isolat2.ent isonum.ent isopub.ent mmlextra.ent mmlalias.ent soextblx.dtd fig1a.tif fig2d.tif fig3a.tif fig4a.tif
us-declaration	dec1.tif
us-declaration	dec2.tif
Comments	